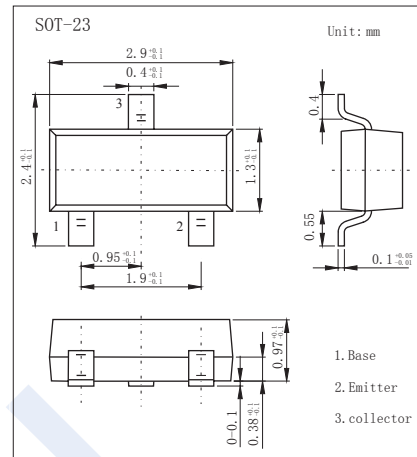


## PNP Transistors

## BCW68 (KCW68)

## ■ Features

- Complementary to BCW66, BCW68 is subdivided into three groups F, G and H according to its DC current gain.

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CB0}$	-60	V
Collector - Emitter Voltage	$V_{CE0}$	-45	
Emitter - Base Voltage	$V_{EB0}$	-5	
Collector Current - Continuous	$I_c$	-800	mA
Collector Power Dissipation	$P_c$	330	mW
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature range	$T_{stg}$	-55 to 150	

## PNP Transistors

## BCW68 (KCW68)

## ■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V <sub>CB0</sub>	I <sub>c</sub> = -100 μA, I <sub>E</sub> =0	-60			V
Collector- emitter breakdown voltage	V <sub>CE0</sub>	I <sub>c</sub> = -10 mA, I <sub>B</sub> =0	-45			
Emitter - base breakdown voltage	V <sub>EB0</sub>	I <sub>E</sub> = -100 μA, I <sub>C</sub> =0	-5			
Collector-base cut-off current	I <sub>CB0</sub>	V <sub>CB</sub> = -45 V, I <sub>E</sub> =0			-20	nA
Emitter cut-off current	I <sub>EB0</sub>	V <sub>EB</sub> = -4V, I <sub>C</sub> =0			-20	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>c</sub> =-100 mA, I <sub>B</sub> =-10mA			-0.3	V
		I <sub>c</sub> =-500 mA, I <sub>B</sub> =-50mA			-0.7	
Base - emitter saturation voltage	V <sub>BE(sat)</sub>	I <sub>c</sub> =-100 mA, I <sub>B</sub> =-10mA			-1.25	
		I <sub>c</sub> =-500 mA, I <sub>B</sub> =-50mA			-2	
DC current gain	h <sub>FE(1)</sub>	V <sub>CE</sub> = -10V, I <sub>c</sub> = -0.1mA	F	35		
			G	50		
			H	80		
	h <sub>FE(2)</sub>	V <sub>CE</sub> = -1V, I <sub>c</sub> = -10mA	F	75		
			G	120		
			H	180		
	h <sub>FE(3)</sub>	V <sub>CE</sub> = -1V, I <sub>c</sub> = -100mA	F	100		250
			G	160		400
			H	250		630
	h <sub>FE(4)</sub>	V <sub>CE</sub> = -2V, I <sub>c</sub> = -500mA	F	35		
			G	60		
			H	100		
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> = -10V, I <sub>E</sub> = 0, f=1MHz		6		pF
Collector input capacitance	C <sub>ib</sub>	V <sub>EB</sub> = -0.5V, I <sub>E</sub> = 0, f=1MHz		60		
Transition frequency	f <sub>t</sub>	V <sub>CE</sub> = -5V, I <sub>c</sub> = -50mA, f=20MHz		200		MHz

■ Classification of h<sub>FE(3)</sub>

Type	BCW68F	BCW68G	BCW68H
Range	100-250	160-400	250-630
Marking	DF	DG	DH

# PNP Transistors

## BCW68 (KCW68)

■ Typical Characteristics

